Amendments to the Claims

1. (*Currently Amended*) An electric device ~~(1, 100)~~ with a body ~~(2, 101)~~ having a resistor ~~(7, 250)~~ comprising a phase change material being changeable between a first phase and a second phase, the resistor ~~(7, 250)~~ having an electric resistance which depends on whether the phase change material is in the first phase or the second phase, the resistor ~~(7, 250)~~ being able to conduct a current for enabling a transition from the first phase to the second phase, the phase change material being a fast growth material.

2. (*Currently Amended*) An electric device ~~(1, 100)~~ as claimed in Claim 1, wherein the phase change material has a crystallization speed of at least 1 m/s.

3. (*Currently Amended*) An electric device ~~(1, 100)~~ as claimed in Claim 1, wherein the phase change material is a composition of formula $Sb_{1-c}M_c$, with c satisfying $0.05 \leq c \leq 0.61$, and M being one or more elements selected from the group of Ge, In, Ag, Ga, Te, Zn and Sn.

4. (*Currently Amended*) An electric device ~~(1, 100)~~ as claimed in Claim 3, wherein c satisfies $0.05 \leq c \leq 0.5$.

5. (*Currently Amended*) An electric device ~~(1, 100)~~ as claimed in Claim 4, wherein c satisfies $0.10 \leq c \leq 0.5$.

6. (*Currently Amended*) An electric device ~~(1, 100)~~ as claimed in Claim 1, wherein the phase change material is substantially free of Te.

7. (*Currently Amended*) An electric device ~~(1, 100)~~ as claimed in Claim 3, wherein the phase change material comprises ~~Ge and/or Ga~~ Ge or Ga in concentrations which range in total between 5 and 35 atomic percent.

8. (*Currently Amended*) An electric device ~~(1, 100)~~ as claimed in Claim 3, wherein the phase change material comprises ~~In and/or Sn~~ In or Sn in concentrations which range in total between 5 and 30 atomic percent.

9. (*Currently Amended*) An electric device ~~(1, 100)~~ as claimed in Claim 1, wherein the phase change material is a composition of formula $Sb_aTe_bX_{100-(a+b)}$, with a, b and 100–(a+b) denoting atomic percentages satisfying $1 \leq a/b \leq 8$ and $4 \leq 100-(a+b) \leq 22$, and X being one or more elements selected from the group of Ge, In, Ag, Ga, Zn and Sn.

10. (*Currently Amended*) An electric device ~~(1, 100)~~ as claimed in Claim 9, wherein the phase-change material comprises at least 10 % and less than 22 % Ge.

11. (*Currently Amended*) An electric device ~~(100)~~ as claimed in Claim 9, wherein the resistor ~~(7, 250)~~ has a first contact area ~~(5, 132)~~ and a second contact area ~~(6, 272)~~, the first contact area ~~(132)~~ being smaller than or equal to the second contact area ~~(272)~~, the first contact area ~~(132)~~ having a characteristic dimension d (in nm), d being larger than 6·a/b.

12. (*Currently Amended*) An electric device ~~(100)~~ as claimed in Claim 1, wherein the phase change material of the resistor ~~(250)~~ is in direct contact with a crystallization layer ~~(127, 128)~~ for expediting the transition from an amorphous phase to a crystalline phase.

13. (*Currently Amended*) An electric device ~~(100)~~ as claimed in Claim 12, wherein the crystallization layer ~~(127, 128)~~ is in direct contact with the first contact area ~~(132)~~ and/or in direct contact with the second contact area ~~(272)~~.

14. (*Currently Amended*) An electric device ~~(100)~~ as claimed in Claim 1, wherein the resistor ~~(250)~~, a first conductor ~~(130)~~ and a second conductor ~~(270)~~ electrically connected to the resistor ~~(250)~~ constitute a memory element ~~(103)~~, and the body ~~(101)~~ comprises:
[[-]] an array of memory cells, each memory cell comprising a respective memory element ~~(103)~~ and a respective selection device ~~(104)~~, and

[[-]] a grid of selection lines ~~(120, 190)~~,

each memory cell being individually accessible via the respective selection lines ~~(120, 190)~~ connected to the respective selection device ~~(104)~~.

15. (*Currently Amended*) An electric device ~~(100)~~ as claimed in Claim 14, wherein:

[[-]] the selection device ~~(104)~~ comprises a metal oxide semiconductor field effect transistor having a source region ~~(110)~~, a drain region ~~(112)~~ and a gate region ~~(116)~~, and

[[-]] the grid of selection lines comprises N first selection lines ~~(190)~~, M second selection lines ~~(120)~~, N and M being integers, and an output line ~~(271)~~,

_____the first conductor ~~(130)~~ of each memory element ~~(103)~~ being electrically connected to a first region selected from the source region ~~(110)~~ and the drain region ~~(112)~~ of the corresponding metal oxide semiconductor field effect transistor,

_____the second conductor ~~(270)~~ of each memory element ~~(103)~~ being electrically connected to the output line ~~(271)~~, a second region of the corresponding metal oxide semiconductor field effect transistor which is selected from the source region ~~(110)~~ and the drain region ~~(112)~~ and which is free from the first region, being electrically connected to one of the N first selection lines ~~(190)~~,

_____the gate region ~~(116)~~ being electrically connected to one of the M second selection lines ~~(120)~~.

16. (*Original*) An electric apparatus comprising a processor, a memory coupled to the processor, and a display coupled to an output terminal of the processor, wherein the memory comprises an electrical device as claimed in Claim 1.